

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	71	(((controlled or assisted) near growth) same crystalline)	USPAT	OR	OFF	2004/12/08 13:45
L2	42	"5eV"	USPAT	OR	OFF	2004/12/08 13:35
L3	0	2 and 1	USPAT	OR	OFF	2004/12/08 13:33
L4	15	((crystalline near growth) or (growth near3 crystalline)) same "eV"	USPAT	OR	OFF	2004/12/08 13:36

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	35773	((manufacturing or fabricating or making) same ((energy near storage near device) or battery or (fuel near cell) or capacitor))	USPAT	OR	OFF	2004/12/08 11:32
L2	79700	depositing same (film or layer)	USPAT	OR	OFF	2004/12/08 11:33
L3	5099	2 and 1	USPAT	OR	OFF	2004/12/08 11:33
L4	195	energized near ions	USPAT	OR	OFF	2004/12/08 11:36
L5	7	4 and 3	USPAT	OR	OFF	2004/12/08 11:36
L6	136389	("PACD" or "IAD" or "PD" or (plasma near assisted near chemical near vapor near deposition) or (ion near assisted near deposition) or (physical near vapor near deposition) or sputtering)	USPAT	OR	OFF	2004/12/08 12:05
L7	2147	3 and 6	USPAT	OR	OFF	2004/12/08 12:06
L8	61	((assist\$4 near growth) or (control\$4 near growth)) same ((crystal or crystalline) near structure)	USPAT	OR	OFF	2004/12/08 12:19
L9	1	7 and 8	USPAT	OR	OFF	2004/12/08 12:07
L10	56	2 and 4	USPAT	OR	OFF	2004/12/08 12:25
L11	8292	(204/192.1-192.38.ccls. or 204/298.01-298.41.ccls.)	USPAT	OR	OFF	2004/12/08 12:28
L12	119	1 and 11	USPAT	OR	OFF	2004/12/08 12:28